NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI CBSL1** is Designed for UHF Class A Amplifier Applications in Cellular Base Station Equipment.

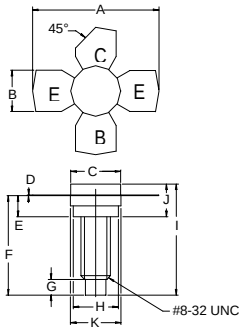
FEATURES:

- **Pg** = 10 dB min. @ 960 MHz
- $\mathbf{P_{1dB}}$ = 1.0 Watts min. at 960 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

$\mathbf{I_C}$	0.25 A
$\mathbf{V_{CBO}}$	40 V
$\mathbf{V_{CEO}}$	28 V
$\mathbf{V_{EBO}}$	3.5 V
$\mathbf{P_{DISS}}$	7.0 W @ T_C = 25 ^{O}C
$\mathbf{T_J}$	-65 ^{O}C to +200 ^{O}C
$\mathbf{T_{STG}}$	-65 ^{O}C to +150 ^{O}C
$\mathbf{\theta_{JC}}$	25 ^{O}C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10577

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$\mathbf{BV_{CBO}}$	I_C = 1.0 mA			40			**V**
$\mathbf{BV_{CEO}}$	I_C = 1.0 mA			25			**V**
$\mathbf{BV_{EBO}}$	I_E = 1.0 mA			3.5			**V**
$\mathbf{I_{CBO}}$	V_{CB} = 24 V					500	**µA**
$\mathbf{h_{FE}}$	V_{CE} = 5.0 V	I_C = 100 mA		20		120	**---**
$\mathbf{C_{OB}}$	V_{CB} = 28 V		f = 1.0 MHz			5.0	**pF**
$\mathbf{P_G}$ $\mathbf{P_{1dB}}$	V_{CC} = 24 V	I_{CQ} = 125 mA	f = 960 MHz	10 1.0			**dB** **W**

Specifications are subject to change without notice.